



- L2: (40835) 1 and dielectric
- L3: (2286) 2 and (barrier with conduct\$3)
- L4: (873) 3 and ((upper or above or top) ac
- L5: (673) 4 and ((barrier adj4 (conduct\$ or
- L6: (217) 5 and (oxygen with diffusi\$3)
- L7: (206) 6 and (dielectric.clm. or conduct
- L8: (174) 7 and ((first or second or upper
- L9: (119) 8 and barrier.clm.
- L10: (99) 9 and ((oxygen adj diffusi\$3) or
- L11: (99) 10 and capacitor
- L12: (92) 11 and capacitor.clm.
- L13: (42) 12 and (atomic or precurs\$3 or cl
- L14: (28) 13 and (atomic or chemisor\$4)
- L15: (11) 14 and (atomic adj3 (layer or mat

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DBs: USPAT; US-PGPUB ☒ Plurals

Default operator: OR ☒ Highlight all hit terms initially

14 and (atomic adj3 (layer or material or barrier))

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	F
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030001186 A1	20030102		Semiconductor memory device capable of preventing oxidation of plug and	257/300	257/295; 257/298;	
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020190276 A1	20021219		Process for the formation of RuSixOy-containing barrier layers	257/200		
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020153550 A1	20021024		FRAM and method of fabricating the same	257/301	257/296	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020121697 A1	20020905		Process for the formation of RuSixOy-containing barrier layers	257/751		
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020000598 A1	20020103		Semiconductor devices having metal layers as barrier layers on upper	257/301	257/310	
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20010024387 A1	20010927		Conformal thin films over textured capacitor electrodes	365/200		
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20010020715 A1	20010913		Semiconductor device and manufacturing method therefor	257/310	438/306	
9	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6509601 B1	20030121	35	Semiconductor memory device having capacitor protection layer and	257/310	257/306; 257/324;	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6180447 B1	20010130	13	Methods for fabricating integrated	438/240	438/396	



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